

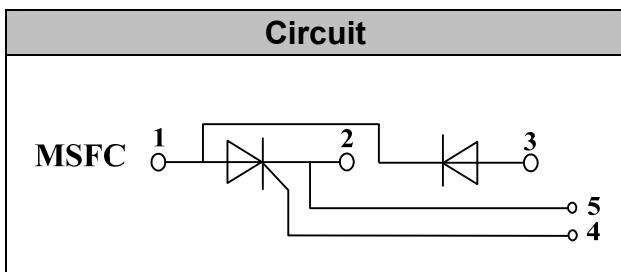


Thyristor/Diode Modules

V_{RRM} / V_{DRM} 800 to 1600V
I_{FAV} / I_{TAV} 130Amp

Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control



Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DBCceramic isolated metal baseplate
- UL E243882 approved

Module Type

TYPE	V _{RRM/V_{DRM}}	V _{RSM}
MSFC130-08	800V	900V
MSFC130-12	1200V	1300V
MSFC130-16	1600V	1700V

◆ Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I _D	Output Current(D.C.)	T _c =85°C	130	A
I _{FSM}	Surge forward current	t=10mS T _{vj} =45°C	4700	A
i ² t	Circuit Fusing Consideration		110000	A ² s
V _{Isol}	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T _{vj}	Operating Junction Temperature		-40 to +125	°C
T _{stg}	Storage Temperature		-40 to +125	°C
M _t	Mounting Torque	To terminals(M6)	3±15%	Nm
M _s		To heatsink(M6)	5±15%	Nm
Weight	Module (Approximately)		165	g

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
R _{th(j-c)}	Thermal Impedance, max.	Junction to Case	0.09	°C/W
R _{th(c-s)}	Thermal Impedance, max.	Case to Heatsink	0.05	°C/W

Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V _{FM}	Forward Voltage Drop, max.	T=25°C I _F =500A			1.80	V
I _{RRM}	Repetitive Peak Reverse Current, max.	T _{vj} =25°C V _{RD} =V _{RRM} T _{vj} =125°C V _{RD} =V _{RRM}		≤0.5 ≤9		mA mA

◆Thyristor
Maximum Ratings

Symbol	Item	Conditions	Values	Units
I _{TAV}	Average On-State Current	Sine 180°; T _c =85°C	130	A
I _{TSM}	Surge On-State Current	T _{VJ} =45°C t=10ms, sine T _{VJ} =125°C t=10ms, sine	4700 4000	A
i ² t	Circuit Fusing Consideration	T _{VJ} =45°C t=10ms, sine T _{VJ} =125°C t=10ms, sine	110000 80000	A2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T _{VJ}	Operating Junction Temperature		-40 to +130	°C
T _{STG}	Storage Temperature		-40 to +125	°C
M _T	Mounting Torque	To terminals(M6)	3±15%	Nm
M _S		To heatsink(M6)	5±15%	Nm
di/dt	Critical Rate of Rise of On-State Current	T _{VJ} = T _{VJM} , 2/3V _{DRM} , I _G =500mA Tr<0.5us, tp>6us	200	A/us
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	T _J =T _{VJM} , 2/3V _{DRM} linear voltage rise	1000	V/us
a	Maximum allowable acceleration		50	m/s ²

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
R _{th(j-c)}	Thermal Impedance, max.	Junction to Case	0.18	°C/W
R _{th(c-s)}	Thermal Impedance, max.	Case to Heatsink	0.10	°C/W

Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V _{TM}	Peak On-State Voltage, max.	T=25°C I _T =500A			1.8	V
I _{RRM} /I _{DRM}	Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max.	T _{VJ} =T _{VJM} , V _R =V _{RRM} , V _D =V _{DRM}			40	mA
V _{TO}	On state threshold voltage	For power-loss calculations only (T _{VJ} =125°C)			1	V
r _T	Value of on-state slope resistance, max	T _{VJ} =T _{VJM}			1.6	mΩ
V _{GT}	Gate Trigger Voltage, max.	T _{VJ} =25°C, V _D =6V			3	V
I _{GT}	Gate Trigger Current, max.	T _{VJ} =25°C, V _D =6V			150	mA
V _{GD}	Non-triggering gate voltage, max.	T _{VJ} =125°C, V _D =2/3V _{DRM}			0.25	V
I _{GD}	Non-triggering gate current, max.	T _{VJ} =125°C, V _D =2/3V _{DRM}			10	mA
I _L	Latching current, max.	T _{VJ} =25°C, R _G =33 Ω		300	1000	mA
I _H	Holding current, max.	T _{VJ} =25°C, V _D =6V		150	400	mA
t _{gd}	Gate controlled delay time	T _{VJ} =25°C, IG=1A, dI _G /dt=1A/us			1	us
t _q	Circuit commutated turn-off time	T _{VJ} =T _{VJM}			100	us

Performance Curves

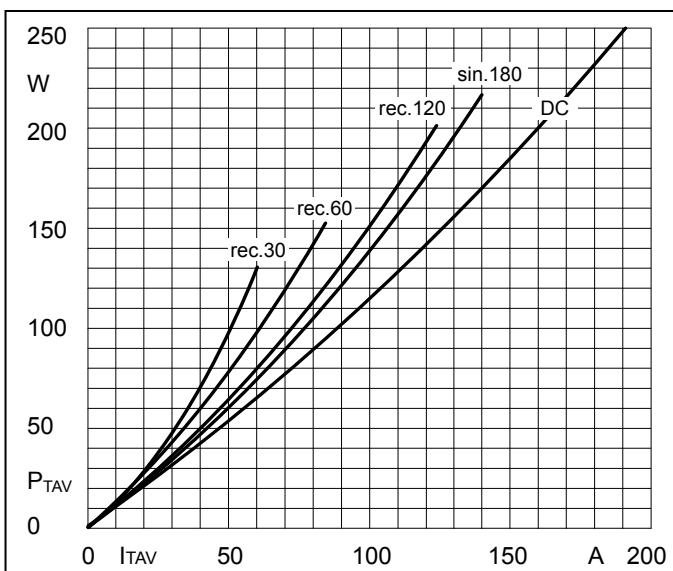


Fig1. Power dissipation

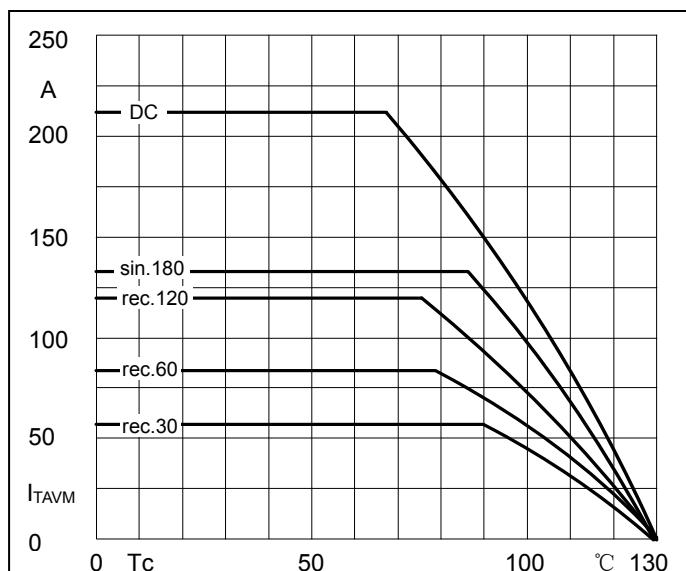


Fig2. Forward Current Derating Curve

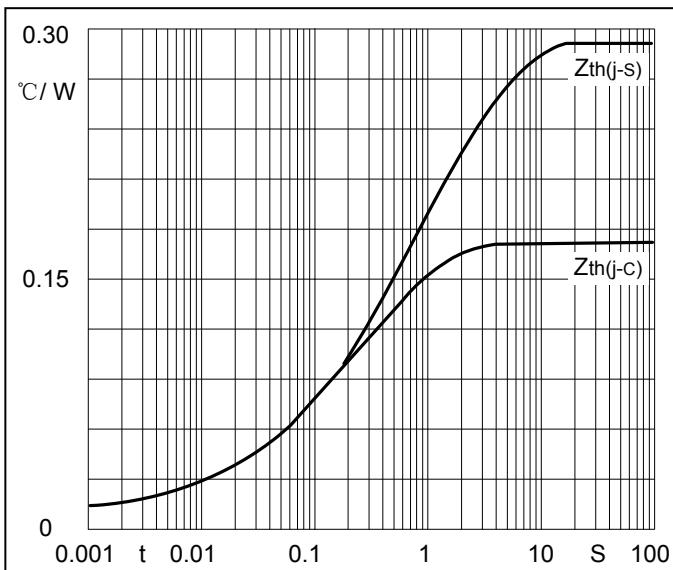


Fig3. Transient thermal impedance

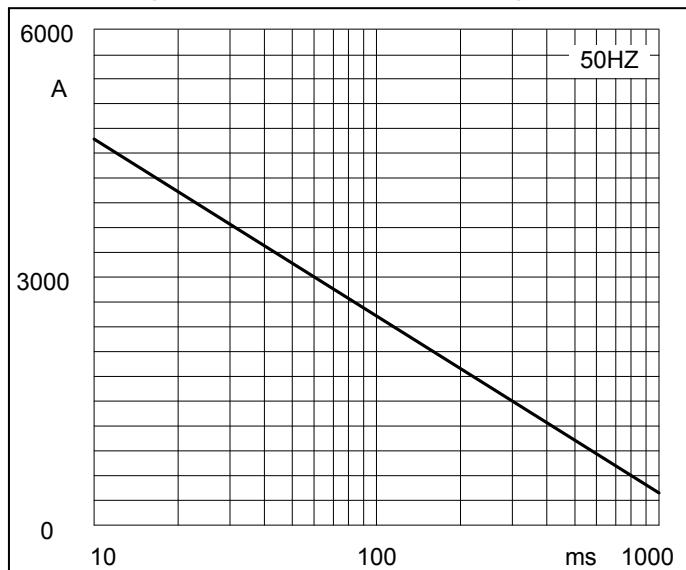


Fig4. Max Non-Repetitive Forward Surge Current

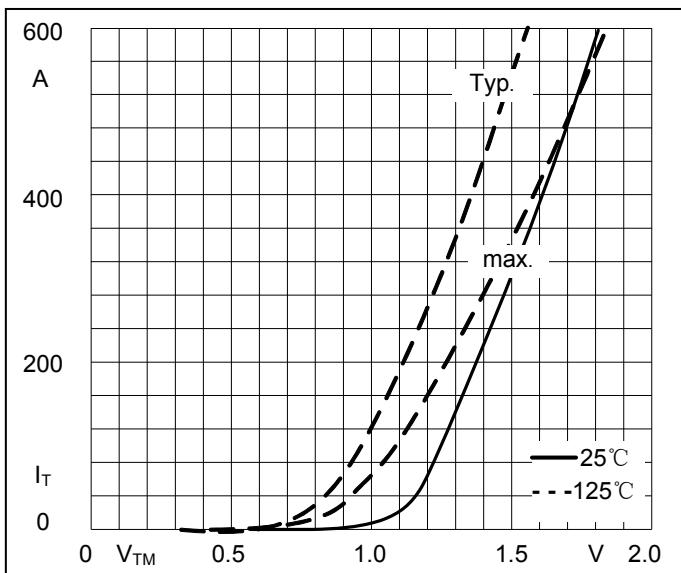


Fig5. Forward Characteristics

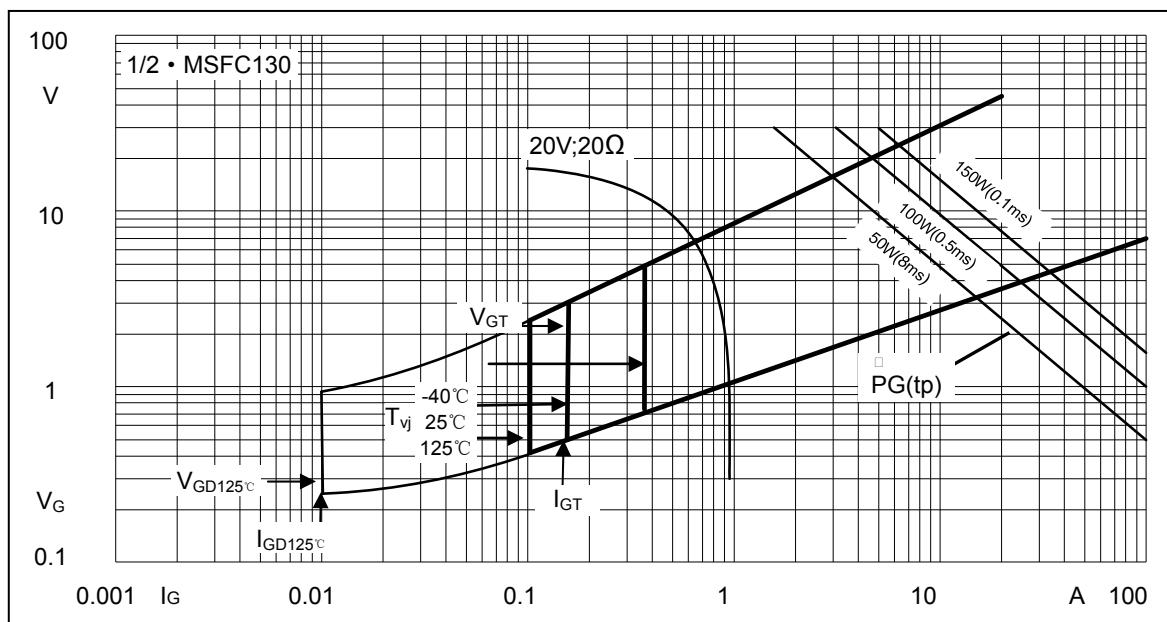


Fig6. Gate trigger Characteristics

Package Outline Information

